

In the Specification:

Please amend the paragraph beginning at page 2, line 2 of the application as filed as follows:

This is a continuation of U.S. Patent Application Serial No. 09/022,763, filed on February 12, 1998, now U.S. Patent No. 6,175,184, entitled BUFFERED RESIST PROFILE ETCH OF A FIELD EMISSION DEVICE STRUCTURE, from which divisional U.S. Patent Application Serial No. 09/404,913, now U.S. Patent No. 6,190,930 was filed on September 24, 1999, both of which are herein incorporated by reference in their entirety.

Please replace the Abstract of the Invention at page 28, lines 2-14 with the following new Abstract:

-- A field emission device comprises an emitter tip that is optionally formed from and integral with an emitter layer. The emitter tip has a base, an apex, and an exterior surface having a profile between the base and the apex. The profile has a continuous shape that extends from the base to the apex. The devices may be part of a flat panel display device that also includes a substrate, a cathode conductive layer disposed over the substrate, an array of emitter tips each formed from an emitter layer disposed over the substrate, a conductive gate structure disposed over the cathode conductive layer, an array of apertures formed through the conductive gate structure, and an anode panel for emitting light in response to electrons emitted from the array of emitter tips.--